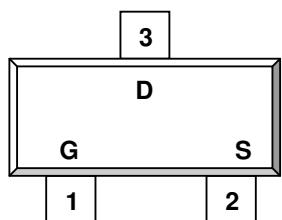


TASUND**2N7002**

N Channel Enhancement Mode MOSFET

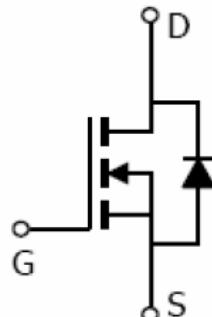
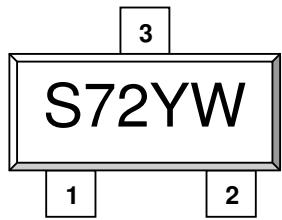
300mA

**PIN CONFIGURATION
SOT-23**

1.Gate 2.Source 3.Drain

FEATURE

- 60V/0.30A, $R_{DS(ON)} = 5\Omega$ @ $V_{GS} = 10V$ (Typ.)
- 60V/0.25A, $R_{DS(ON)} = 7\Omega$ @ $V_{GS} = 4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and Maximum DC current capability
- SOT-23 package design

**PART MARKING
SOT-23**

Y : Year Code W : Process Code



2N7002



N Channel Enhancement Mode MOSFET

300mA

ABSOULTE MAXIMUM RATINGS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current TJ=150°C)	I _D	0.3	A
Pulsed Drain Current	I _{DM}	1.0	A
Power Dissipation	P _D	0.35	W
Operation Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	375	°C/W



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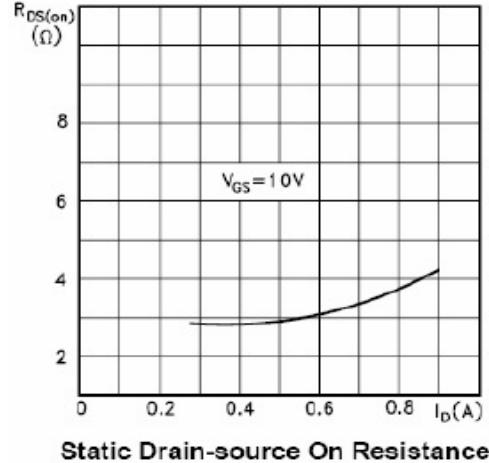
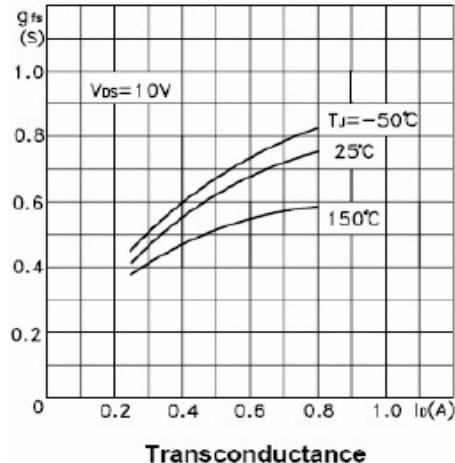
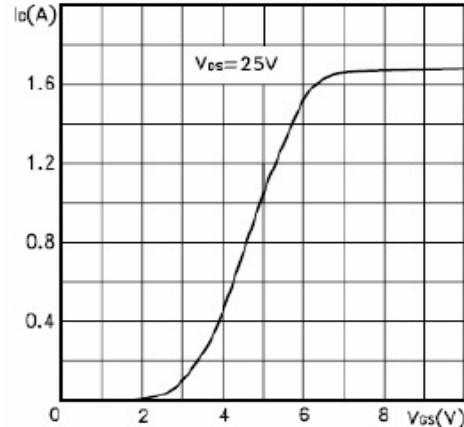
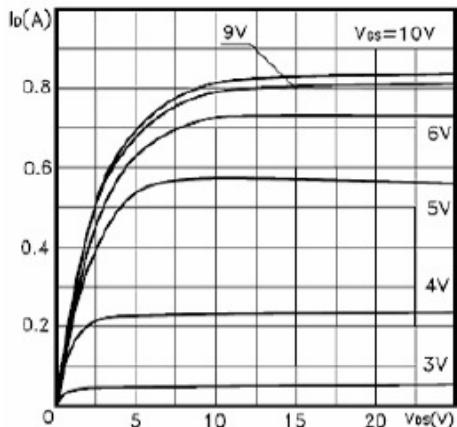
N Channel Enhancement Mode MOSFET

300mA

ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D = 250uA	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = 250uA	0.8		2.5	V
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 45V, V _{GS} =0V			1	uA
		V _{DS} = 45V, V _{GS} =0V T _J =125°C			10	
On-State Drain Current On-State Drain Current (plsed)	I _{SD(on)} I _{SDM(2)}				0.35 1.4	A
Drain-source On-Resistance	R _{DS(on)}	V _{GS} =10.0V, I _D =0.50A V _{GS} =4.5V, I _D = 0.25A		2.50 3.30	6.0 7.0	Ω
Forward Transconductance	G _{fs(1)}	V _{DS} =10V, I _D = 0.5A		0.6		S
Diode Forward Voltage	V _{SD(1)}	I _s =0.12A, V _{GS} =0V		0.85	1.5	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =30V, V _{GS} =4.5V I _D ≡1.0A		1.4	2.0	nC
Gate-Source Charge	Q _{gs}			0.8		
Gate-Drain Charge	Q _{gd}			0.5		
Input Capacitance	C _{iss}	V _{DS} =25V, f=1MHz, V _{GS} =0		43		pF
Output Capacitance	C _{oss}			20		
Reverse Transfer Capacitance	C _{rss}			6		
Turn-On Time	t _{d(on)} tr	V _{DD} =30V I _D =0.5A V _{GS} =4.5V R _G =4.7Ω		6		nS
Turn-Off Time	t _{d(off)} tf			15		
				6	13	
				7	9	

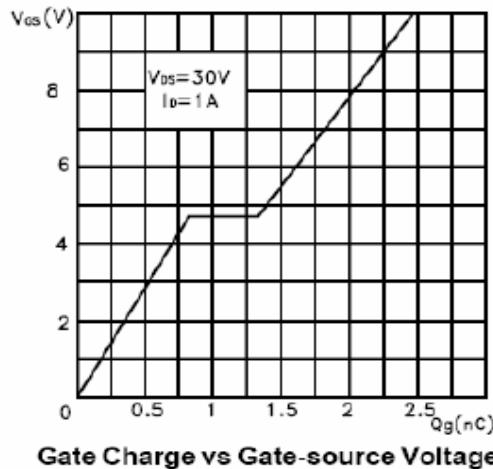
TYPICAL CHARACTERISTICS (25°C Unless noted)



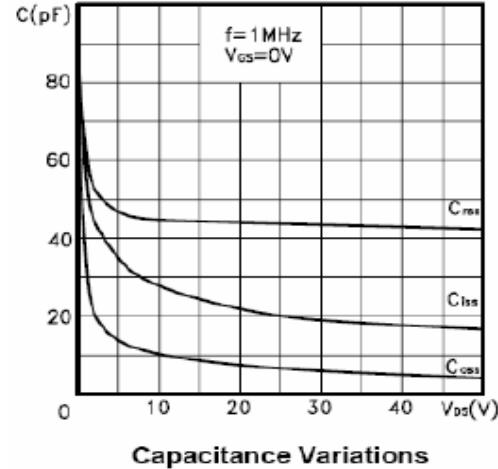
TASUND**2N7002**

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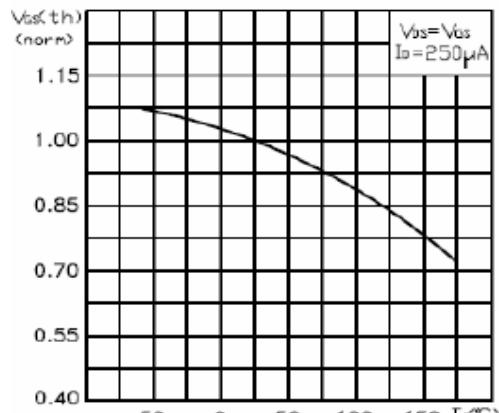
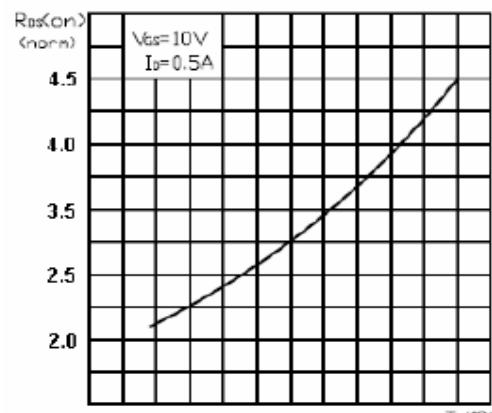
300mA

TYPICAL CHARACTERISTICS

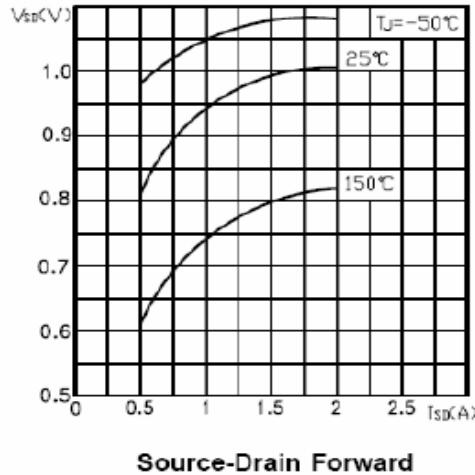
Gate Charge vs Gate-source Voltage



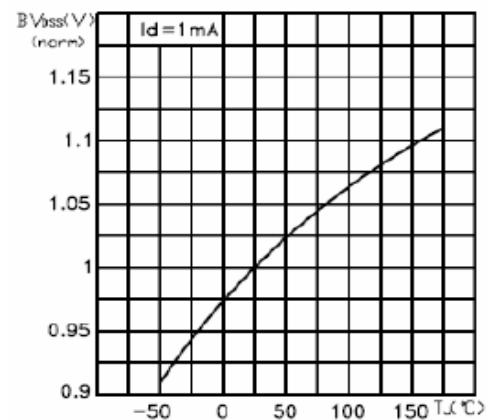
Capacitance Variations

Normalized Gate Threshold Voltage
vs TemperatureNormalized On Resistance
vs Temperature

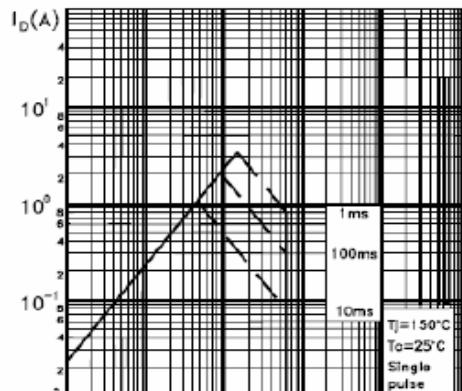
TYPICAL CHARACTERISTICS



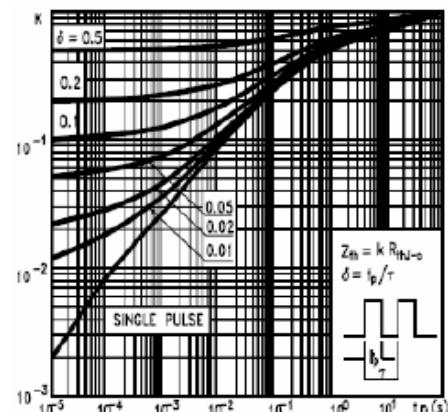
Source-Drain Forward



Normalized BV_{DSS} vs Temperature



Safe Operating Area



Thermal Impedance

TASUND

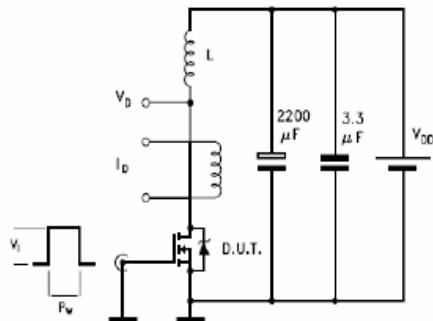
2N7002



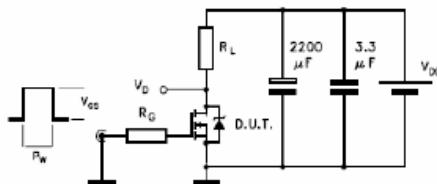
N Channel Enhancement Mode MOSFET

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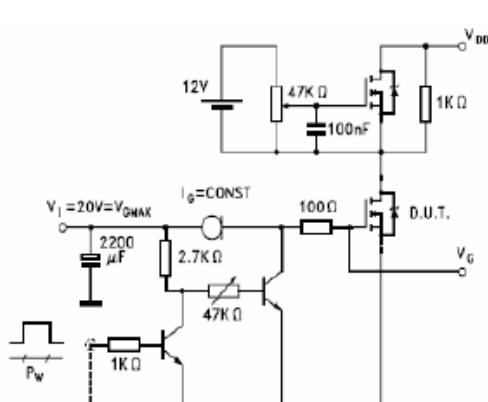
TYPICAL TESTING CIRCUIT



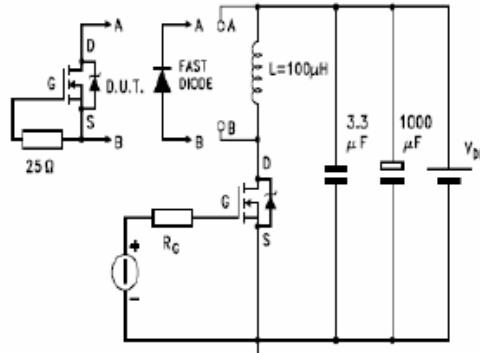
Unclamped Inductive Load Test



Switching Times Test Circuit



Gate Charge Test Circuit



Test Circuit For Inductive Load
Switching and Diode Recovery Times

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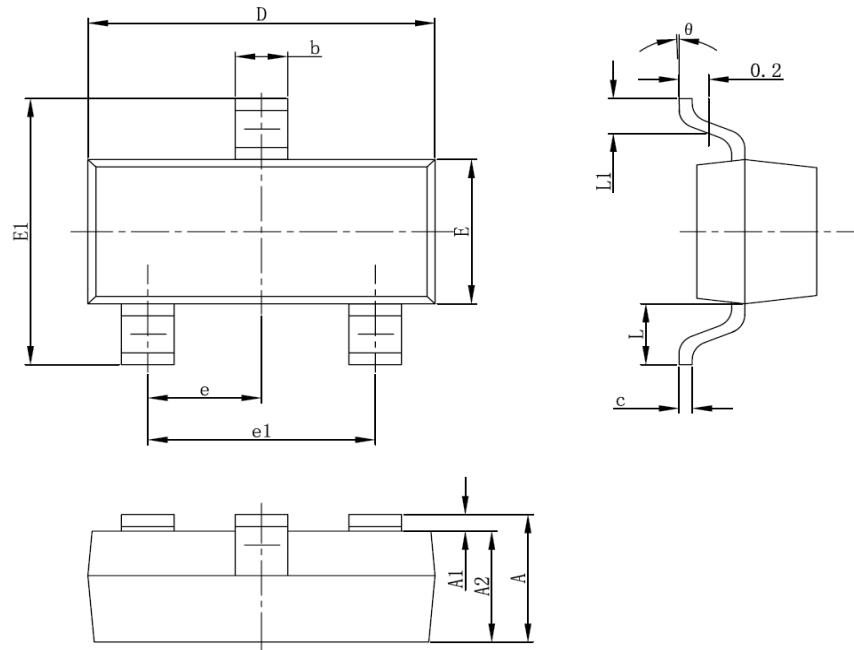
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N Channel Enhancement Mode MOSFET

300mA

SOT-23 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
theta	0°	8°	0°	8°